Nch 600V 15A Power MOSFET

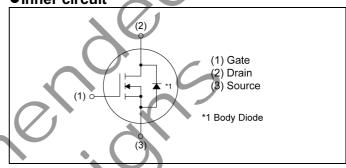
V _{DSS}	600V
R _{DS(on)} (Max.)	0.35Ω
I _D	±15A
P _D	77W

TO-220FM

Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30 \text{V}$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

•Inner circuit



Packaging specifications

or ackaging specimeations							
	Packing	Bulk					
0	Reel size (mm)	-					
	Tape width (mm)	-					
Туре	Basic ordering unit (pcs)	500					
	Taping code	-					
	Marking	R6015FNX					

Application

Switching Power Supply

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

Parameter	/1	Symbol	Value	Unit
Drain - Source voltage		V _{DSS}	600	V
Continuo de decino cumo et	T _C = 25°C	I _D *1	±15	А
Continuous drain current	T _C = 100°C	I _D *1	±7.3	А
Pulsed drain current		I _{DP} *2	±60	Α
Gate - Source voltage		V_{GSS}	±30	V
Avalanche current, single pulse		I _{AS} *3	7.5	Α
Avalanche energy, single pulse		E _{AS} *3	15	mJ
Avalanche energy, repetitive		E _{AR} *4	3.5	mJ
Power dissipation (T _c = 25°C)		P _D	77	W
Junction temperature	T _j	150	°C	
Operating junction and storage temper	T _{stg}	-55 to +150	°C	
Reverse diode dv/dt		dv/dt	15	V/ns

Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_{D} = 15A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Min	Values Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{ ext{thJC}}$	-(-	1.62	°C/W
Thermal resistance, junction - ambient	R _{thJA}	7	-	70	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}		-	265	°C

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values		Unit	
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = 1mA$	600	-	-	V
Drain - Source avalanche breakdown voltage	V _{(BR)DS}	$V_{GS} = 0V, I_D = 7.5A$	ı	700	-	V
		$V_{DS} = 600V, V_{GS} = 0V$				
Zero gate voltage drain current	J _{DSS}	$T_j = 25^{\circ}C$	-	1	100	μΑ
X	7	$T_j = 125^{\circ}C$	-	-	10000	
Gate - Source leakage current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 1mA	3	-	5	V
		V _{GS} = 10V, I _D = 7.5A				
Static drain - source on - state resistance	R _{DS(on)} *6	$T_j = 25^{\circ}C$	-	0.27	0.35	Ω
on state regionality		$T_j = 125^{\circ}C$	-	0.59	-	
Gate resistance	R_G	f = 1MHz, open drain	-	10.2	-	Ω

● Electrical characteristics (T_a = 25°C)

Dougnoston	Cymaela a l	Conditions	Values			Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward Transfer Admittance	Y _{fs} *6	V _{DS} = 10V, I _D = 7.5A	4.5	10	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	1	1660		•
Output capacitance	C _{oss}	V _{DS} = 25V	-	1110		pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	45	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V,		54.6	-	F
Effective output capacitance, time related	C _{o(tr)}	V _{DS} = 0V to 480V		183	-	pF
Turn - on delay time	t _{d(on)} *6	V _{DD} ≈ 300V, V _{GS} = 10V	-	38)	-	
Rise time	t _r *6	I _D = 7.5A		45	-	
Turn - off delay time	t _{d(off)} *6	$R_L \simeq 40.2\Omega$	1	120	240	ns
Fall time	t _f *6	$R_G = 10\Omega$	J	35	70	

● Gate charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions		Values		Unit
	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{\star 6}$	V _{DD} ≈ 300V	-	42	-	
Gate - Source charge	Q _{gs} *6	I _D = 15A	-	12	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	20	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 300V$, $I_D = 15A$	-	7.6	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw ≤ 10μs, Duty cycle ≤ 1%

^{*3} L \simeq 500 μ H, V_{DD}=50V, R_G=25 Ω , starting T_j = 25°C

^{*4} L $^{\sim}500\mu\text{H},\,\text{V}_{DD}$ =50V, R $_{G}$ =25 Ω , starting T $_{j}$ = 25 $^{\circ}\text{C},\,\text{f}$ = 10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Darameter	Cumabal	Canditions	Values			l limit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	I _S *1	T - 25°C	-	-	15	А
Pulse forward current	I _{SP} *2	T _C = 25°C	-	- 6	60	A
Forward voltage	V_{SD}^{*6}	$V_{GS} = 0V, I_{S} = 15A$	-	- *	1.5	V
Reverse recovery time	t _{rr} *6		-	90	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 15A di/dt = 100A/µs		0.44	-	μC
Peak reverse recovery current	I _{rrm} *6	α//ατ = 100/4/μ5		10.4	-	Α
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C)-	1000	-	A/µs

Typical transient thermal characteristics

,	Symbol	Value	Unit
	R _{th1}	0.117	
•	R _{th2}	0.662	k/W
	R _{th3}	2.14	•

Symbol	Value	Unit
C _{th1}	0.00318	
C _{th2}	0.0429	Ws/K
C_{th3}	0.507	

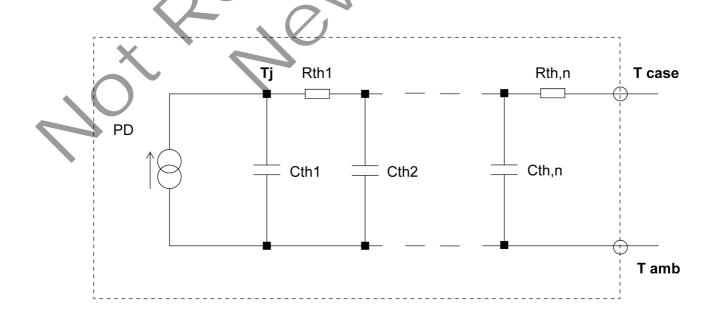


Fig.1 Power Dissipation Derating Curve

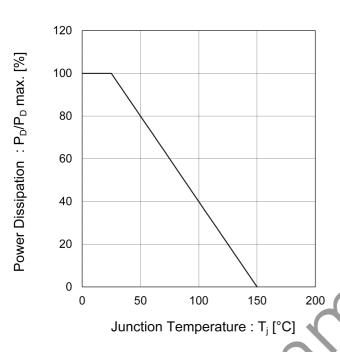


Fig.2 Maximum Safe Operating Area

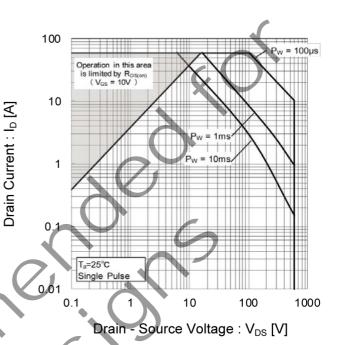


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

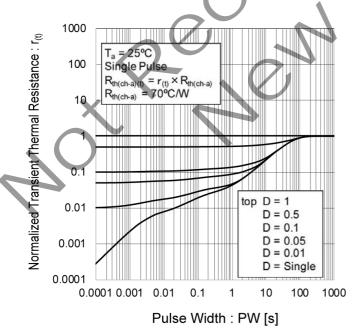
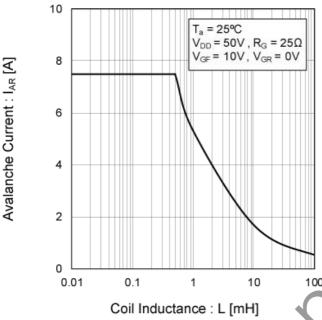


Fig.4 Avalanche Current vs. Inductive Load

Fig.5 Avalanche Power Losses 5000



T_a = 25°C 4500 Avalanche Power Losses : PAR [W] 4000 3500 3000 2500 2000 1500 1000 1.0E+04 1.0E+05 1.0E+06

Frequency: f [Hz]

Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature

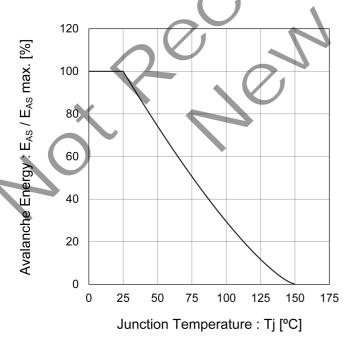


Fig.7 Typical Output Characteristics(I)

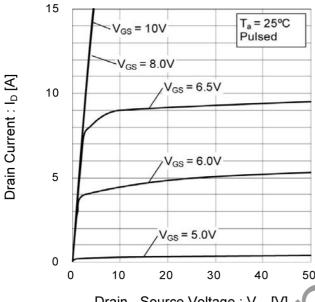
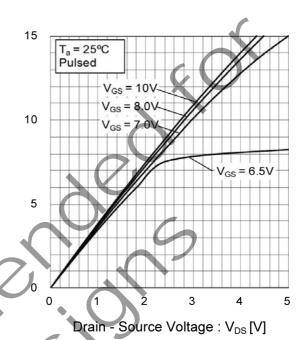


Fig.8 Typical Output Characteristics(II)



Drain Current : I_D [A]

Drain - Source Voltage : $V_{DS}[V]$

Fig.9 Tj = 150°C Typical Output Characteristics (I)

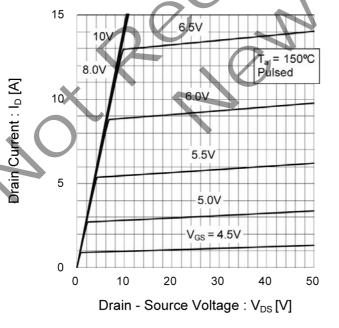
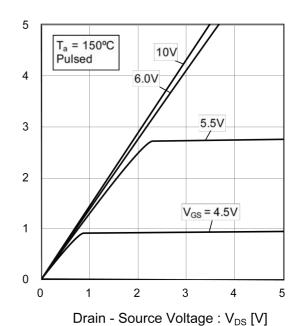


Fig.10 Tj = 150°C Typical Output Characteristics (II)



Drain Current: I_D [A]

Fig.11 Breakdown Voltage vs. Junction Temperature

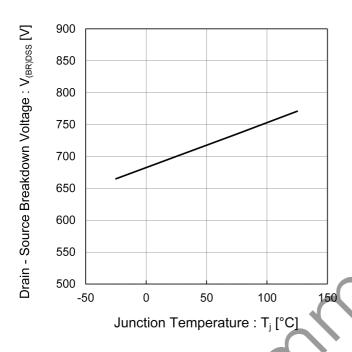


Fig.12 Typical Transfer Characteristics

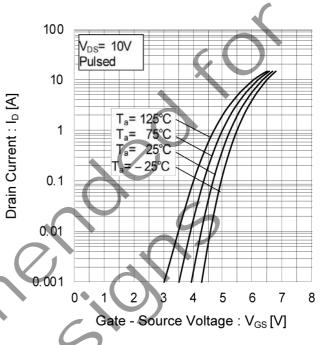


Fig.13 Gate Threshold Voltage vs. Junction Temperature

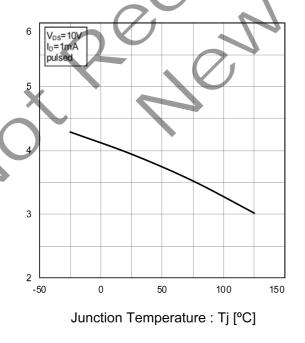
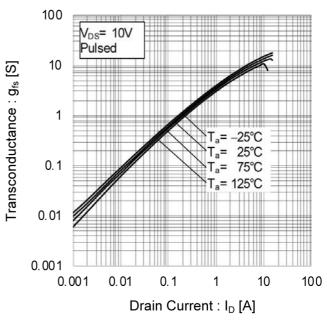


Fig.14 Transconductance vs. Drain Current



Gate Threshold Voltage: V_{GS(th)} [V]

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

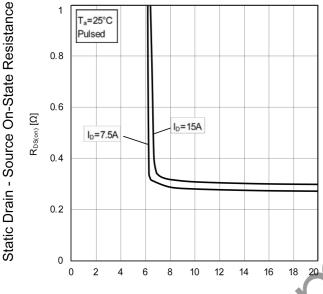
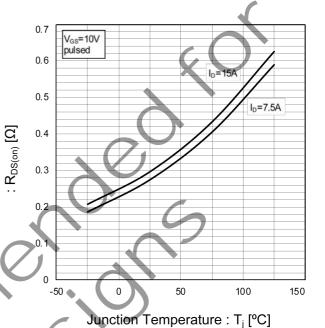
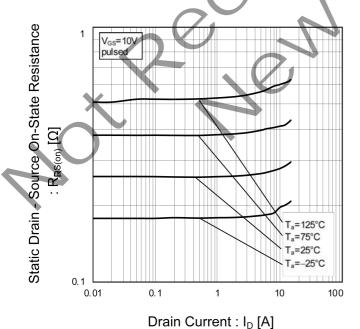


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature



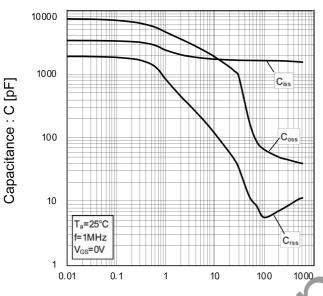
Gate - Source Voltage : Vgs [V]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



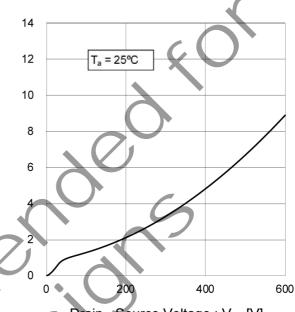
atic Drain - Source On-State Resistance

Fig.18 Typical Capacitance vs. Drain - Source Voltage



Drain - Source Voltage : V_{DS} [V]

Fig.19 Coss Stored Energy



Coss Stored Energy : E $_{
m oss}$ [μ J]

Drain - Source Voltage : V_{DS} [V]

Fig.20 Switching Characteristics

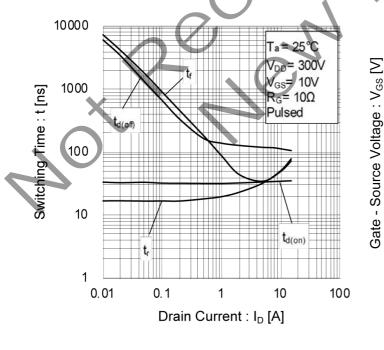
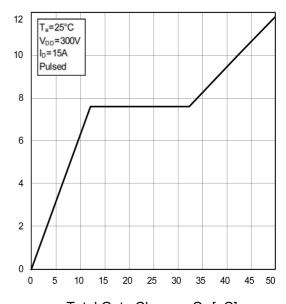


Fig.21 Dynamic Input Characteristics



Total Gate Charge : Qg [nC]

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

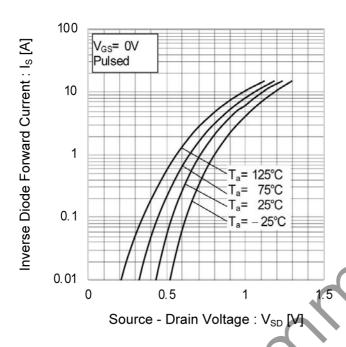
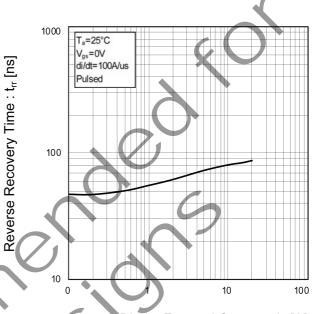


Fig.23 Reverse Recovery Time vs.
Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

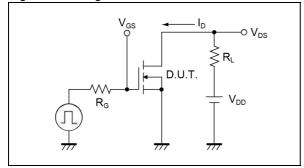


Fig.2-1 Gate Charge Measurement Circuit

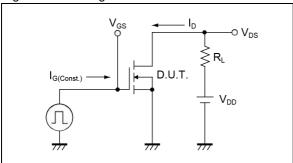


Fig.3-1 Avalanche Measurement Circuit

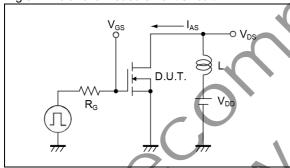


Fig.4-1 dv/dt Measurement Circuit

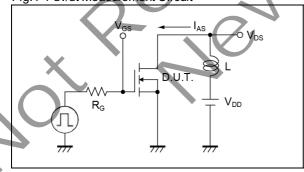


Fig.5-1 di/dt Measurement Circuit

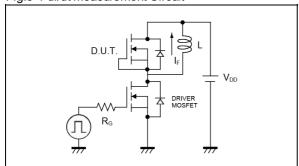


Fig.1-2 Switching Waveforms

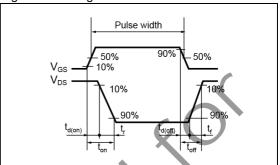


Fig.2-2 Gate Charge Waveform

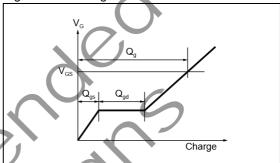


Fig.3-2 Avalanche Waveform

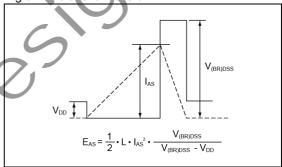


Fig.4-2 dv/dt Waveform

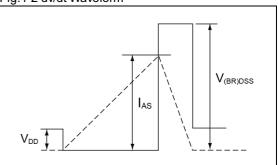
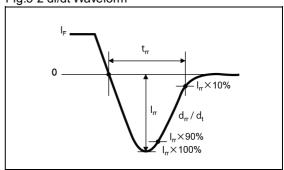
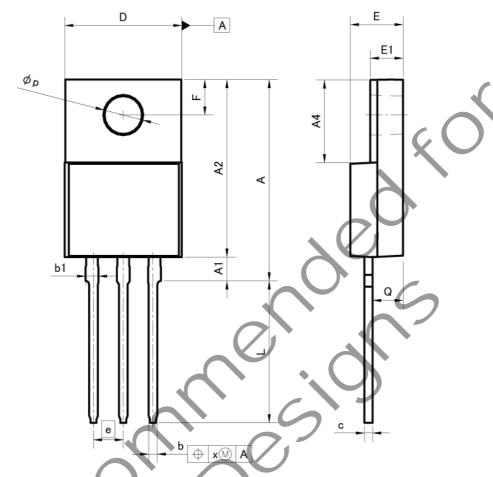


Fig.5-2 di/dt Waveform



Dimensions





			15	
DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
ь	0.70	0.90	0.028	0.035
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.390	0.406
E	4.40	4.80	0.173	0.189
е	2.	54	0.1	00
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.110	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
X	5 <u>—</u> 5	0.38	<u>20</u> 6	0.015

Dimension in mm/inches



Notice

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JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSII	CLASS II b	CLASSIII
CLASSIV		CLASSⅢ	

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 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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